

Dry-Etch Resistance Data  
of  
SEPR-I803D  
VS  
SEPR-I801

DUV-44 on Si Substrate  
(FT:250nm , Mask : 200nm)

Film Thickness:250 nm Prebake: 110°Cx90 sec

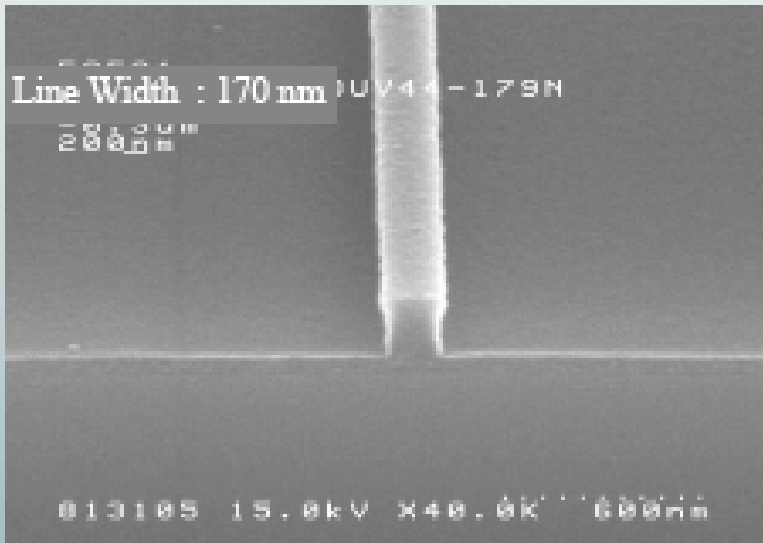
Exp.: 40mJ/cm<sup>2</sup> (NSR-S203B , NA = 0.68,  $\sigma = 0.75$ )

Mask: 200nm (Line Space =1/10) Focus: -0.3 $\mu$ m (Best Focus)

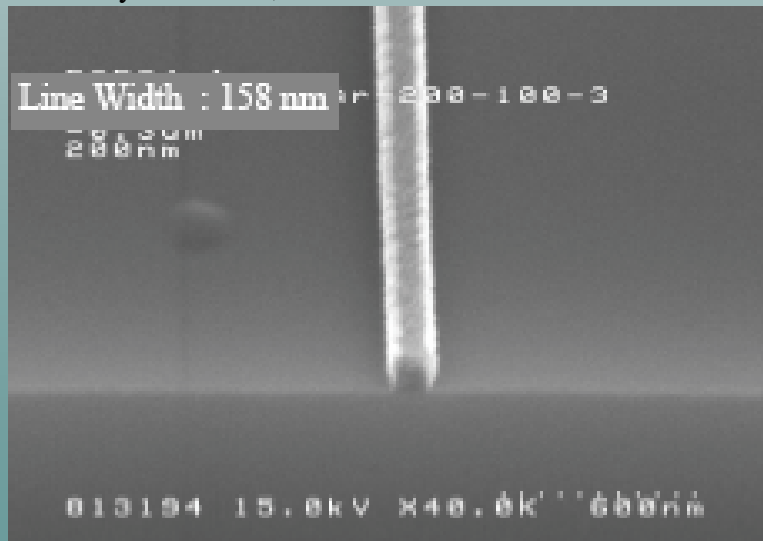
PEB: 110°C x 90 sec

Dev.: 60 sec x 1 puddle (SSF-D-179N [TMAH = 1.79%])

After Dev.



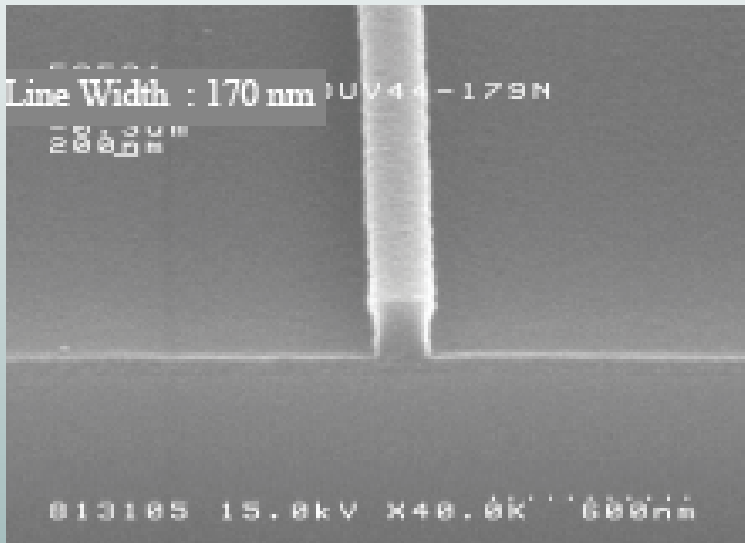
After Dry-Etch : Ar , 100 W X 3 min



# SEPR-I801 Dry-Etch Resistance Data

DUV-44 on Si Substrate  
(FT:250nm , Mask : 200nm)

Film Thickness:250 nm    Prebake: 110°Cx90 sec  
Exp.: 30mJ/cm<sup>2</sup> (NSR-S203B ,    NA = 0.68,  $\sigma$  = 0.75)  
Mask: 200nm (Line Space =1/10)    Focus: -0.3 $\mu$ m (Best Focus)  
PEB: 110°C x 90 sec  
Dev.: 60 sec x 1 puddle (SSF179N [TMAH = 1.79%])  
After Dev.



After Dry-Etch : Ar , 100 W X 3 min

